

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of forming a super self-aligned bipolar transistor with enhanced electrical characteristics. The power gain and frequency response of the transistor
5 are improved by horizontally etching an area for the base region that is wider than the active emitter and collector regions. By removing polysilicon layers within the device, the base region resistance goes down and unwanted capacitive effects are reduced.

MAXM-265/SSK